

Schottky barrier on the InGaAs/InP heterostructures grown by the CL-VPE technique for photodetectors

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Abstract

The Schottky barriers of Ag, Ti, Ni, on n and p iso-type heterostructures of In/sub 0.53/Ga/sub 0.47/As/InP, grown by the CL-VPE technique, have shown that values of 0.6 eV for Ag/p-InGaAs barrier height and of 0.46 eV on n-InGaAs, by growing an n-InP interlayer may be obtained.